

ABSTRACT

Bipolar transistors and methods for fabricating bipolar transistors are disclosed wherein an emitter-base dielectric stack is formed between emitter and base structures, comprising a carbide layer situated between first and second oxide layers. The carbide layer provides an etch stop for etching the overlying
5 oxide layer, and the underlying oxide layer provides an etch stop for etching the carbide layer to form an emitter-base contact opening.